IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Atsushi KUROKAWA et al.

Appln. No.:

Filed: HEREWITH

For: METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants wish to make of record the documents cited in prior Application No. 10/347,806 filed January 22, 2003, whether cited by Applicants or by the Patent Office. The documents are listed on the attached Form PTO-1449.

Respectfully submitted,

MWS:sjk

Miles & Stockbridge P.C. 1751 Pinnacle Drive Suite 500 McLean, Virginia 22102-3833 (703) 903-9000

September 30, 2003

By:

Mitchell W. Shapiro Reg. No. 31,568

FORM PTO-1449					Atty. Docket No.		Appln	Appln. No.	
			27 25	DI TONIT	XA-9801A				
LIST	OF D	OCUMENTS CI	TED BY AP	Applicant		l			
					Atsushi KUROKAWA et al.				
					Filing Date Group HEREWITH				
			U.S.	PATENT DO	CUMENTS				
Examiner Initial		Document Number	Date		lame	Class	Sub- class	Filing Date	
	AA	5,077,231	12/31/91	Plumton	et al.	438	170		
	AB	5,166,083	11/24/92	Bayrakta	roglu	438	170		
	AC	5,268,315	12/07/93	Prasad e	t al.	438	314		
	AD	5,324,671	06/28/94	Bayrakta		438	317		
	AE	5,672,522	09/30/97	Streit e	t al.	438	312		
	AF								
	AG								
	AH					-			
	AI				DOCUMENTUS.				
			FOREIC		DOCUMENTS	Class	Sub-	Translation	
Examiner Initial		Document Number Date		Country		Class	class		
	AJ	2001-210723	08/03/01	Japan				Abstract	
	AK								
	AL								
	AM						 		
	AN								
	AO	1					<u> </u>		
		OTHER	(including a	ithor, title,	date, pertinent	pages, et	c.)	Collector	
		Chen et al., "High-Speed InGaP/GaAs HBT's Using a Simple Collect Undercut Technique to Reduce Base-Collector Capacitance," IEEE Electron Device Letters, Vol. 18, No. 7, July 1997, pp. 355-357. AQ Ahmari et al., "InGaP/CaAs Heterojunction Bipolar Transistor Groon a Semi-Insulating InGaP Buffer Layer," IEEE Electron Device Letters, Vol. 18, No. 11, November 1997, pp. 559-561.							
	AQ								
	AF								
Examir	ner	1		Da	ate Considere	ed			
		Initial if r		naidored '	whether or no	ot citati	ion is i	in conformanc	
EXAMIN with	NER: MPEP	Initial if r 609; draw li py of this fo	na thrailah	CITATION 1	T HOU TH COL	TOTMOTICO	and no	ot considered	
Includ	ae co	by or curs to	IM WICH HEX						